



Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide

Tech ID: 25741 / UC Case 2016-324-0

BACKGROUND

The development of light emitting devices (LEDs) with optimized materials is essential to increase the overall efficiency of the myriad commercial applications of the LED. Wafer bonding permits extension of the design parameters of these devices by allowing the formation of heterojunctions that are not possible through conventional deposition schemes. Bonding to transparent conductive materials leads to higher efficiency due to enhanced light extraction.

DESCRIPTION

Researchers at the University of California, Santa Barbara have developed a method for bonding transparent conductive oxides on III-nitride materials using wafer bonding techniques. Light emitting devices (LEDs) can be processed using this technique which yields higher efficiency devices than traditional methods and allows for greater design options for fabricating devices such as fully transparent tunnel junction-based III-nitride-based LEDs.

ADVANTAGES

- ▶ Increased light extraction efficiency
- ▶ Greater design options for fabricating devices

APPLICATIONS

- ▶ Fully transparent tunnel junction-based LEDs
- ▶ LEDs

PATENT STATUS

Country	Type	Number	Dated	Case
United States Of America	Issued Patent	11,411,137	08/09/2022	2016-324

RELATED TECHNOLOGIES

- ▶ [III-Nitride Tunnel Junction LED with High Wall Plug Efficiency](#)
- ▶ [III-Nitride Tunnel Junction with Modified Interface](#)

CONTACT

Pasquale S. Ferrari
ferrari@tia.ucsb.edu
tel: .

INVENTORS

- ▶ [DenBaars, Steven P.](#)
- ▶ [Mughal, Asad J.](#)
- ▶ [Speck, James S.](#)
- ▶ [Young, Erin C.](#)

OTHER INFORMATION

KEYWORDS

LED, tunnel junction, wafer bonded, conductive oxide, III-nitride, indfeat, indenergy

CATEGORIZED AS

- ▶ **Energy**
 - ▶ Lighting
 - ▶ Other
- ▶ **Engineering**
 - ▶ Engineering
- ▶ **Semiconductors**
 - ▶ Design and Fabrication

RELATED CASES

2016-324-0

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- ▶ Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- ▶ Methods to Produce and Recycle Substates for III-Nitride Materials with Electrochemical Etching
- ▶ III-Nitride Tunnel Junction with Modified Interface
- ▶ Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- ▶ (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- ▶ Thermally Stable, Laser-Driven White Lighting Device
- ▶ III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- ▶ A Method To Lift-Off Nitride Materials With Electrochemical Etch
- ▶ Activation of P-Type Layers of Tunnel Junctions in Micro-LEDs
- ▶ High-Intensity Solid State White Laser Diode
- ▶ Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- ▶ Epitaxial Light Control Features in Light Emitting Diodes
- ▶ High-Efficiency Vertical Cavity Surface Emitting Laser Fabrication
- ▶ A Wafer-Scale, Low Defect Density Strain Relaxed Template for III-Nitride-Based High Efficiency and High-Power Devices

